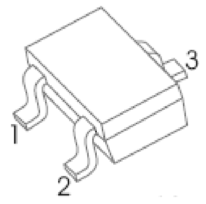
Plastic-Encapsulate Diodes

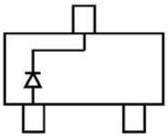
SCHOTTKY BARRIER DIODE

SOT-323

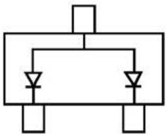


FEATURES

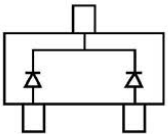
- Low Forward Voltage
- Fast Switching



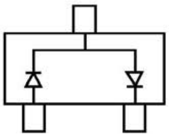
BAS40W



BAS40W-06

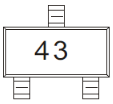
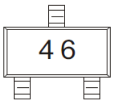
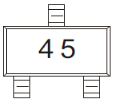
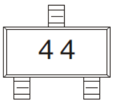


BAS40W-05



BAS40W-04

MARKING:

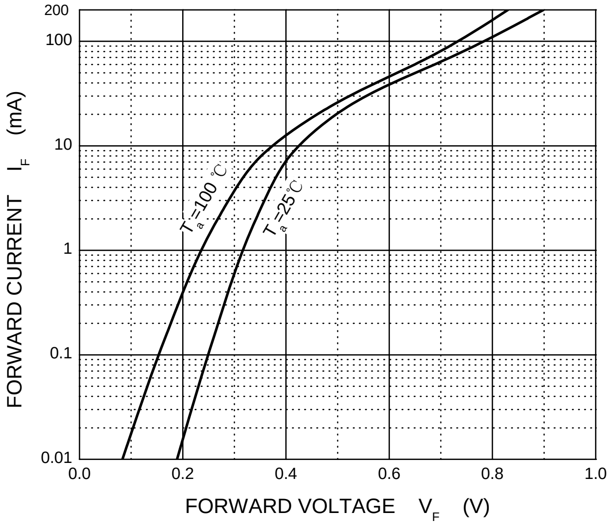
BAS40W	BAS40W-06	BAS40W-05	BAS40W-04
			

Maximum Ratings @Ta=25℃

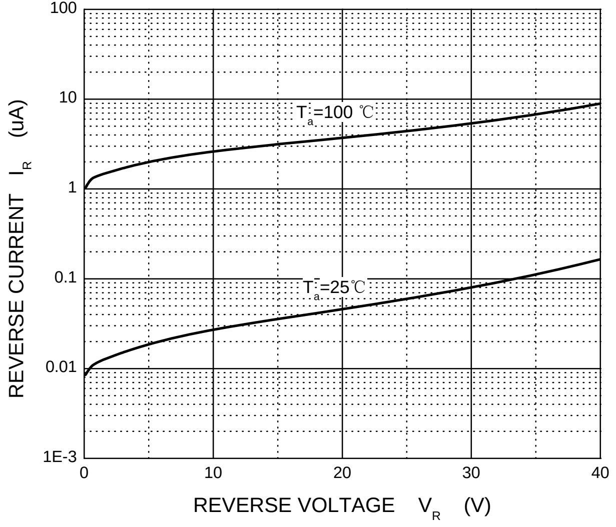
Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage **Working peak reverse voltage** **DC blocking voltage**	V_{RRM} V_{RWM} V_R	40	V
Forward continuous current	I_{FM}	200	mA
Power dissipation	P_D	150	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	667	℃/W
Junction temperature	T_J	125	℃
Storage temperature range	T_{STG}	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

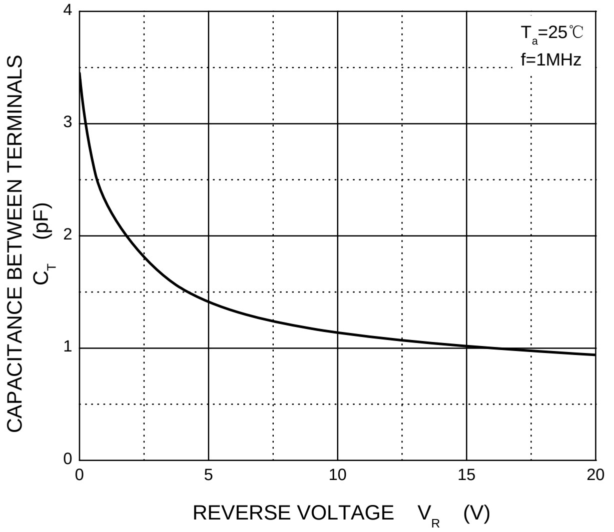
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 10μA	40		V
Reverse voltage leakage current	I_R	V_R=30V		200	nA
Forward voltage	V_F	I_F=1mA I_F=40mA		380 1000	mV
Diode capacitance	C_D	V_R=0,f=1MHz		5	pF
Reverse recovery time	t_{rr}	I_{rr}=1mA, I_R=I_F=10mA R_L=100Ω		5	ns



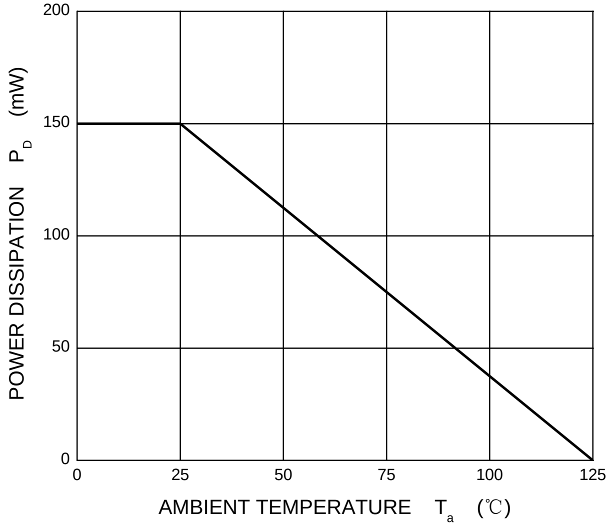
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve